

SANYO	No.1943A	2SA1392/2SC3383
		PNP/NPN Epitaxial Planar Silicon Transistors

AF Amp Applications

Features

- . Adoption of FBET process
- . AF amp

(): 2SA1392

Absolute Maximum Ratings at Ta=25°C

Collector to Base Voltage	V_{CBO}	(-)60	V	unit
Collector to Emitter Voltage	V_{CEO}	(-)50	V	
Emitter to Base Voltage	V_{EBO}	(-)6	V	
Collector Current	I_C	(-)200	mA	
Collector Current (Pulse)	I_{CP}	(-)400	mA	
Collector Dissipation	P_C	400	mW	
Junction Temperature	T_j	150	°C	
Storage Temperature	T_{stg}	-55 to +150	°C	

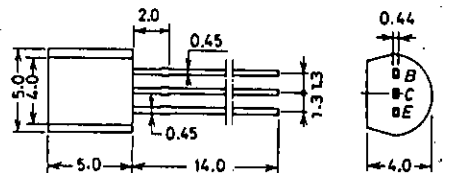
Electrical Characteristics at Ta=25°C

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=(-)40V, I_E=0$			(-)0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=(-)5V, I_C=0$			(-)0.1	μA
DC Current Gain	$h_{FE}(1)$	$V_{CE}=(-)6V, I_C=(-)1mA$	100*		560*	
	$h_{FE}(2)$	$V_{CE}=(-)6V, I_C=(-)0.1mA$	70			
Gain-Bandwidth Product	f_T	$V_{CE}=(-)6V, I_C=(-)10mA$		250		MHz
				(200)		MHz
C-E Saturation Voltage	$V_{CE}(sat)$	$I_C=(-)100mA, I_B=(-)10mA$			(-)0.3	V
B-E Saturation Voltage	$V_{BE}(sat)$	$I_C=(-)100mA, I_B=(-)10mA$			(-)1.0	V
Output Capacitance	c_{ob}	$V_{CB}=(-)6V, f=1MHz$		2.7		pF
				(3.7)		pF
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu A, I_E=0$	(-)60			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1mA, R_{BE}=\infty$	(-)50			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)10\mu A, I_C=0$	(-)6			V

*: The 2SA1392/2SC3383 are classified by 1mA h_{FE} as follows:

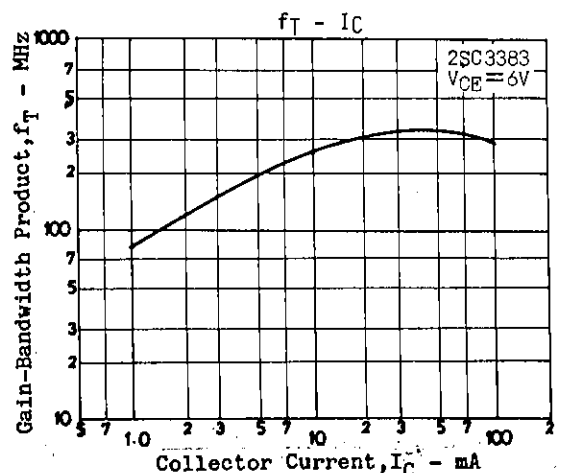
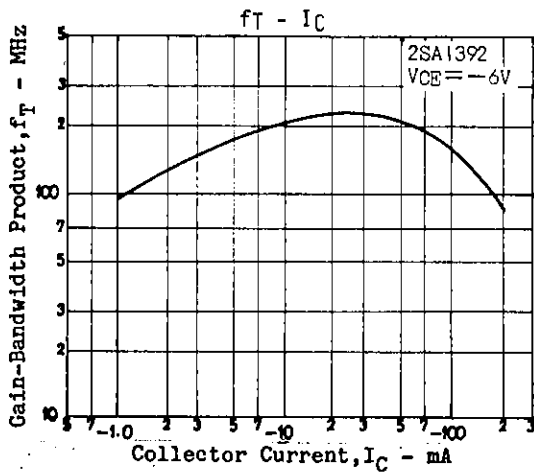
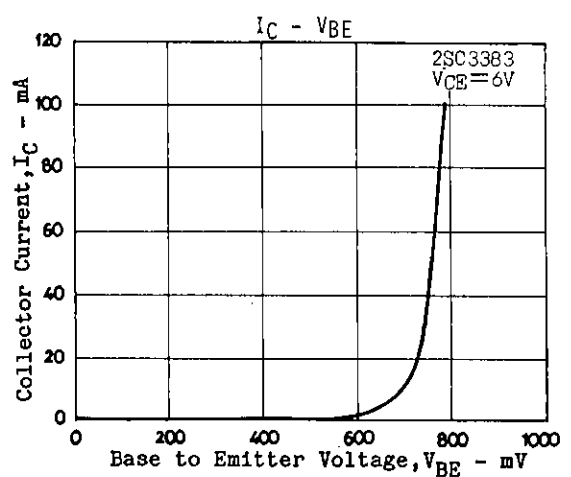
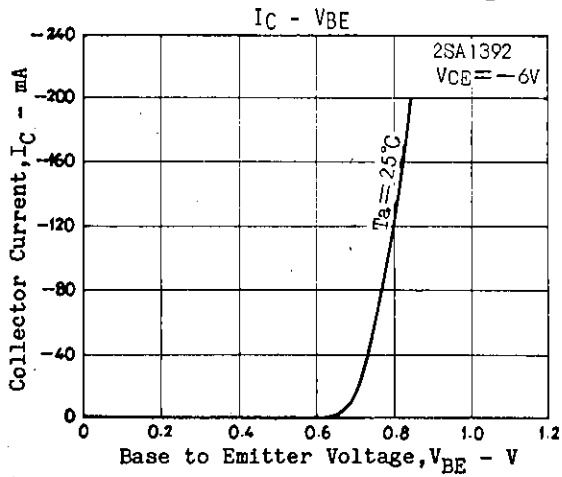
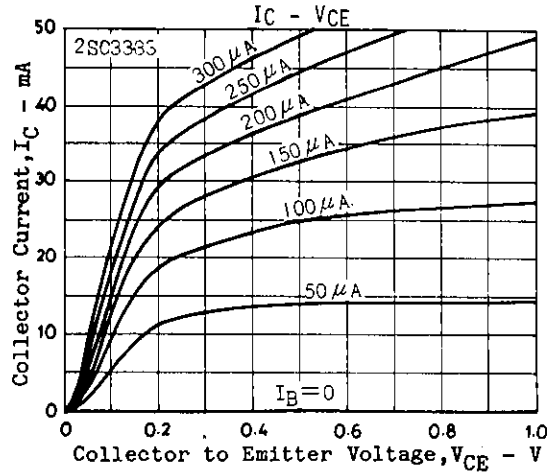
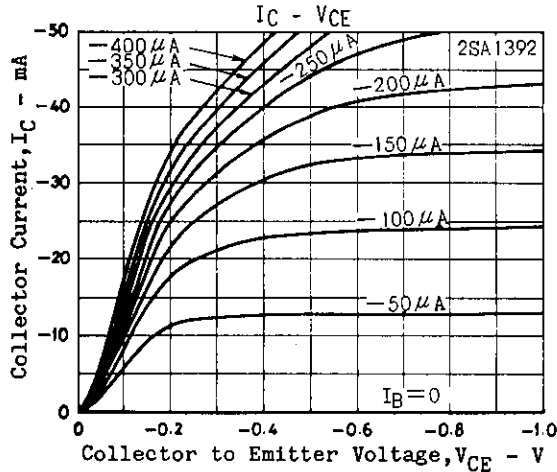
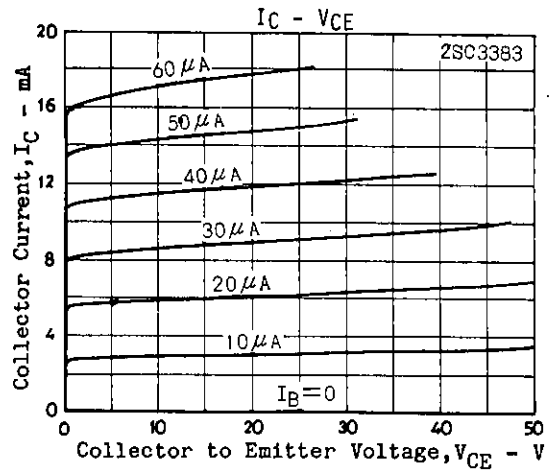
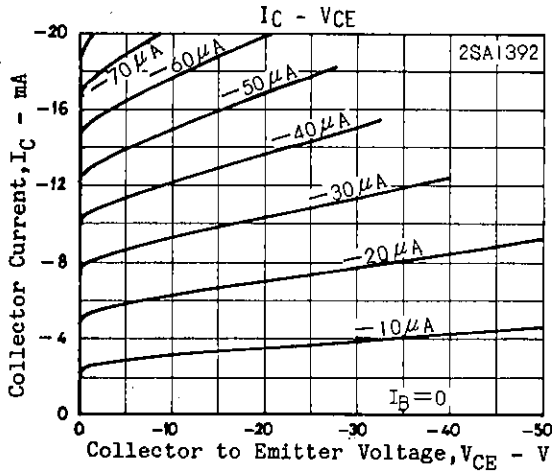
100	R	200	140	S	280	200	T	400	280	U	560
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Package Dimensions 2003A
(unit: mm)

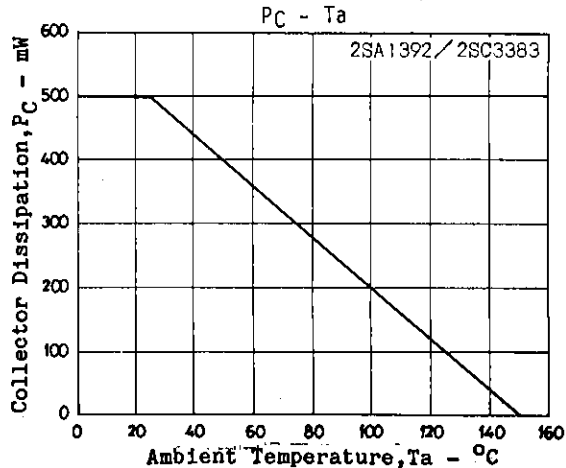
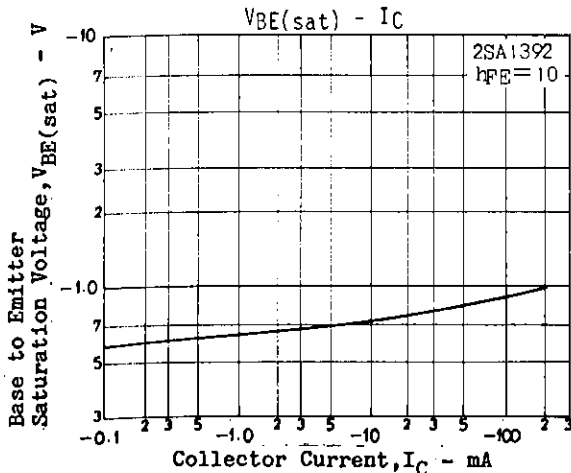
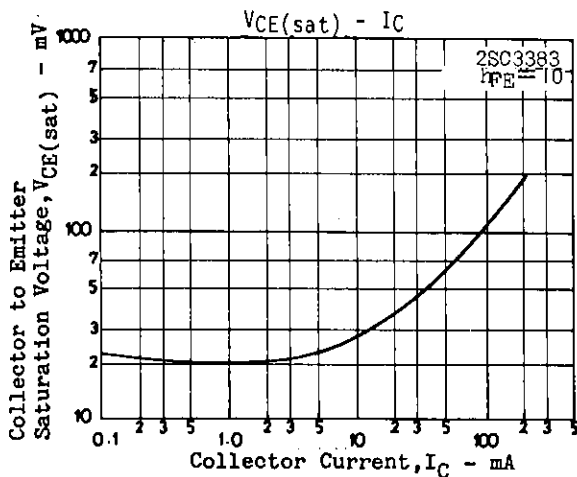
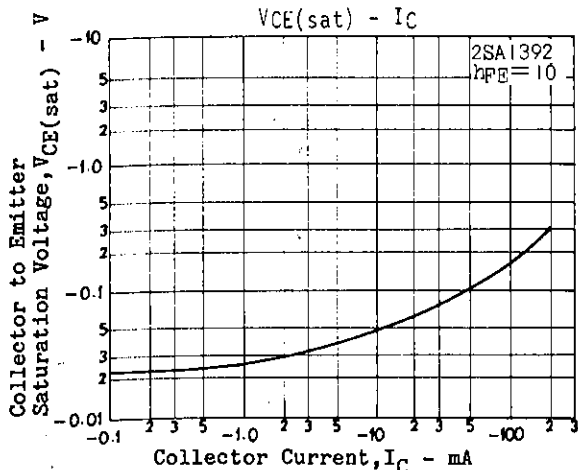
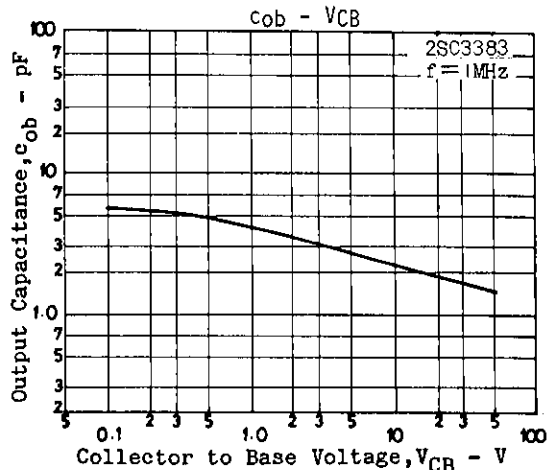
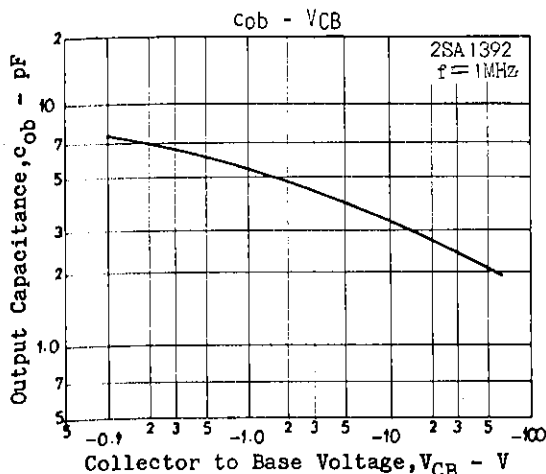
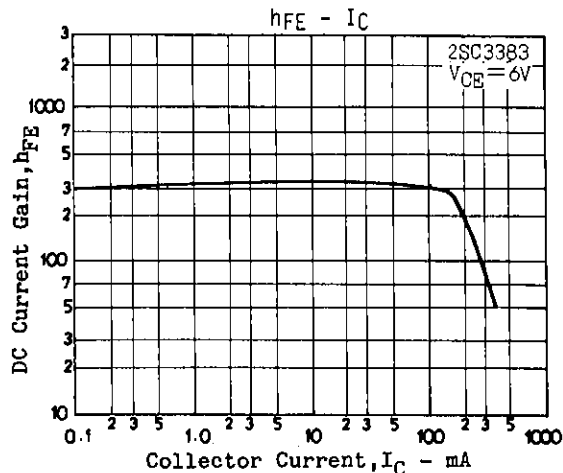
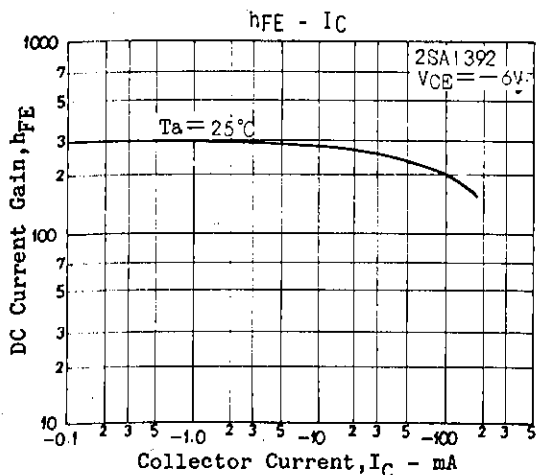


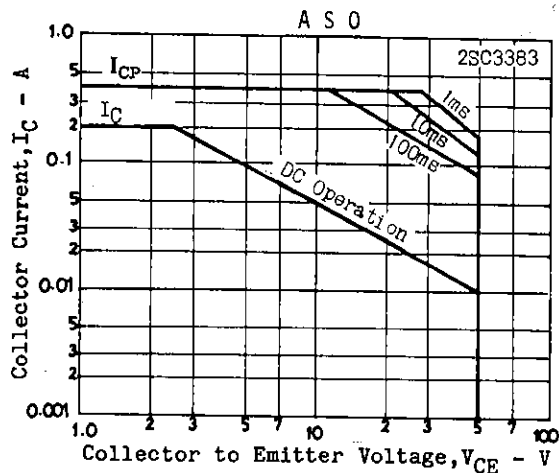
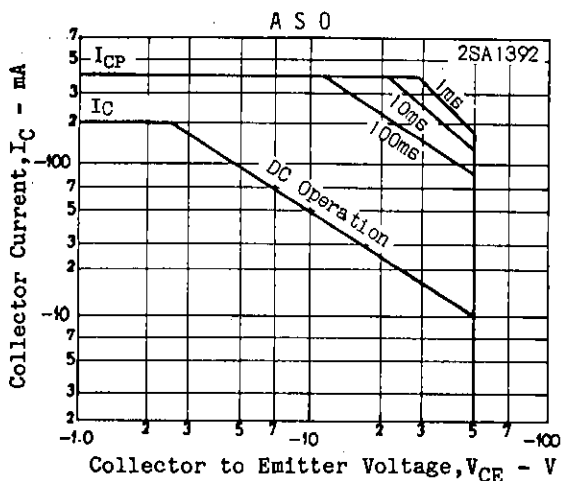
JEDEC: TO-92
EIAJ: SC-43
SANYO: NP

B. Base
C. Collector
E. Emitter



2SA1392/2SC3383





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